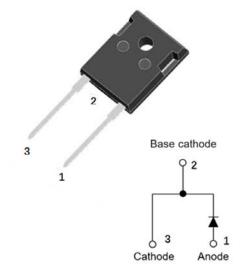


Silicon Carbide Schottky Diode

V _{RRM}	1200V
I _{F (135°C)}	43A
Q _c	162nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- Package: TO-247AC
- Terminals: Tin plated leads
- Polarity: As marked

■Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Device marking code			D112030NQG2
Reverse voltage (Repetitive peak) @ T _j =25°C	V _{RRM}	V	1200
Reverse voltage (Surge peak) @ T _j =25°C	V _{RSM}	V	1200
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	1200
Continuous forward current @ $T_c=25^{\circ}C$		А	94
Continuous forward current @ T_c =135°C	I _F		43
Continuous forward current @ T _c =152°C			30
Non-repetitive peak forward surge current @ $T_c=25^{\circ}C$, tp=10ms, Half Sine Wave	I _{FSM}	А	225
Power Dissipation@ T_c =25°C	Ρτοτ	w	416
Power Dissipation@ T _c =110°C	Гтот	vv	180
i²t Value@ T _c =25°C ,tp=10ms	∫ i²dt	A ² S	253
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175



■Electrical Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Earward voltage drap	V	V	I _F =30A, T _j =25°C	1.43	1.58
Forward voltage drop	V _F	v	I _F =30A, T _j =175°C	1.97	-
Paveraa laakaga aurrant	I _R	μA	V _R =1200V, T _j =25°C	3.4	30
Reverse leakage current			V _R =1200V, T _j =175°C	20.3	-
Total capacitive charge	Q _c	nC	$V_{\text{R}}\text{=}800\text{V},T_{j}\text{=}25^{\circ}\text{C}$, $Q_{\text{C}}\text{=}\int_{0}^{V\text{R}}\text{C}(\text{V})\text{d}\text{V}$	162	-
			V _R =0V, f=1MHZ	2179	-
Total capacitance C	pF	V _R =400V, f=1MHZ	152	-	
			V _R =800V, f=1MHZ	118	-
Capacitance stored energy	Ec	μJ	V _R =800V	42	-

■Thermal Characteristics (Ta=25 °C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{_{ ext{ hetaJ-C}}}$	°C /W	0.36

■Characteristics (Typical)

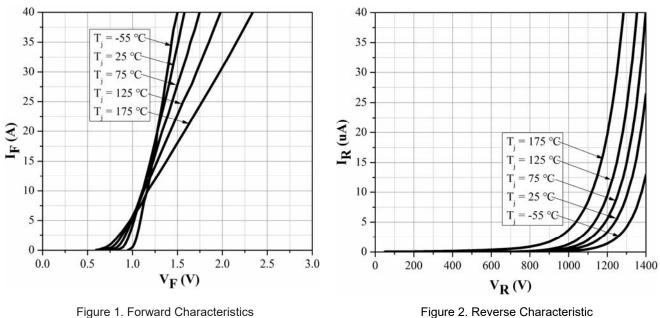


Figure 2. Reverse Characteristic

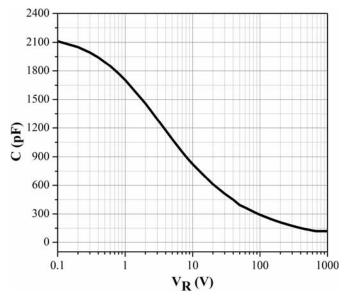
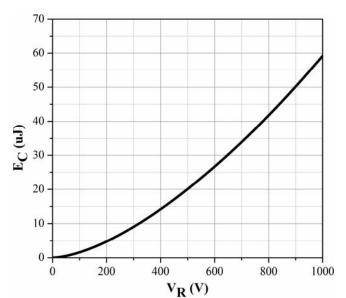
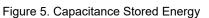
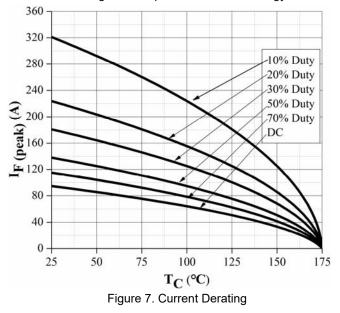


Figure 3. Capacitance vs. Reverse Voltage







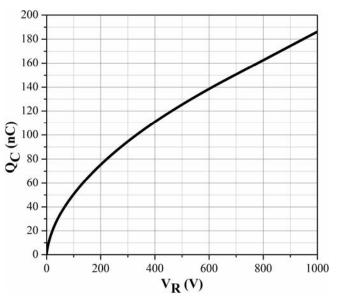
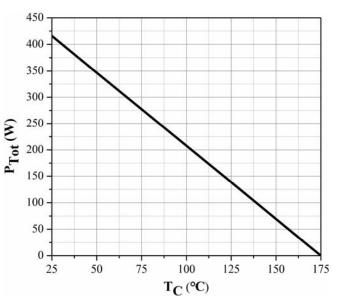
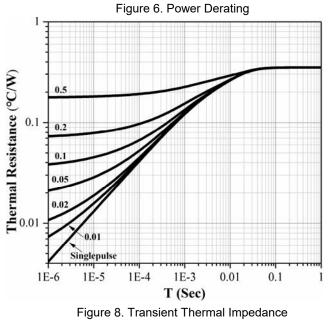


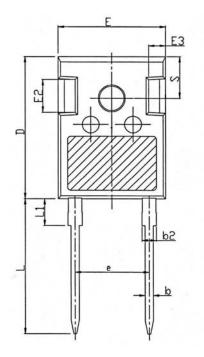
Figure 4. Total Capacitance Charge vs. Reverse Voltage



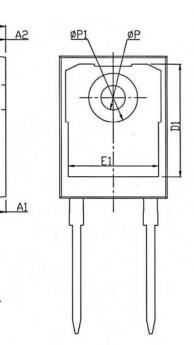




Outline Dimensions



2



TO247-AC				
Dim	Min	Max		
Α	4.80	5.20		
A1	2.21	2.61		
A2	1.85	2.15		
b	1.11	1.36		
b2	1.91	2.21		
с	0.51	0.75		
D	20.70	21.30		
D1	16.25	16.85		
E	15.50	16.10		
E1	13.00	13.60		
E2	4.80	5.20		
E3	2.30	2.70		
е	10.88BSC			
L	19.62	20.22		
L1	-	4.30		
φP	3.40	3.80		
φP1	-	7.30		
S	6.15BSC			



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